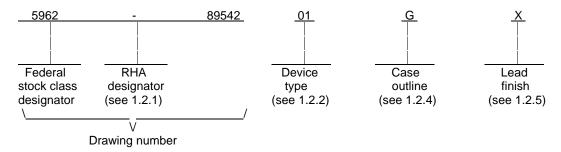
								F	REVISI	ONS										
LTR	DESCRIPTION									DATE (YR-MO-DA)				APPROVED						
Α	Add Upda	device ate boil	type 03 erplate	3. Add to refle	case o	utline H	I. Add ements	radiatio	on hard	ness re	equirem	ents.	00-07-12				R. MONNIN			
В	Make changes to TCV _{OS} , I _{OS} , I _{IB} , CMRR, V _O , PSRR, SR, GE as specified under table I. Make change to figure 1. Add sub table IIA ro						BW, P bgroup	_D tests 7 to		00-10-23			R. MONNIN							
THE ORIGINAL REV SHEET	. FIRST	SHEE	T OF T	HIS DF	RAWIN	G HAS	BEEN	REPL/	ACED.											
REV	. FIRST	SHEE	T OF T	HIS DF	RAWIN	G HAS	BEEN	REPL/	ACED.											
SHEET	. FIRST	SHEE	T OF T	HIS DF	RAWIN	G HAS	BEEN	REPLA	ACED.											
REV SHEET REV	. FIRST	SHEE	T OF TI	HIS DF		G HAS	BEEN	REPL/	ACED.	В	В	В	В	В	В	В	В	В		
REV SHEET REV SHEET	. FIRST	SHEE	T OF T			G HAS				B 4	B 5	B 6	B 7	B 8	B 9	B 10	B 11	B 12		
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A			T OF TI	REV SHE PREI Rick	/ EET PAREL k Office	D BY er	В	В	В		5	6 EFEN	7 SE SI	8 UPPL	9 Y CE	10	11 COL	12 _UMB	US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAI	NDAF	RD	T OF T	REV SHE PREI Rick	/ EET	D BY er	В	В	В		5	6 EFEN	7	8 UPPL	9 Y CE	10	11 COL	12 _UMB	US	
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAT MICRO DRA THIS DRAWIN FOR US DEPAR	NDAF OCIRO AWIN NG IS A SE BY RTMEN	RD CUIT G	BLE	REV SHE PREI Rick	/ EET PAREI k Office	D BY eusing	В	В	В	MIC OP	DI DI CROC ERAT	6 EFEN CIRCUTION	SE SI COL	UPPL UMBI	y CE JS, O	NTEF	11 R COL 43210	12 LUMB 6		
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAT MICRO DRA THIS DRAWIN FOR US	NDAF OCIRO AWIN NG IS A SE BY RTMEN NCIES O	RD CUIT G	BLE	REV SHE PREI Rick CHE Cha	CKED CKED arles Ro	D BY eusing D BY Frye	B 1	B 2	В	MIC OP	DI CROC	6 EFEN CIRCUTION	SE SI COL	UPPL UMBI	y CE JS, O	NTEF	11 R COL 43210	12 LUMB 6		
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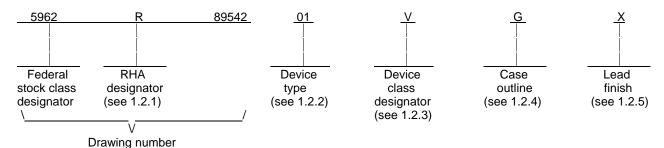
1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



For device class V:



- 1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	OP-15A	JFET-Input, operational amplifier
02	OP-15B	JFET-Input, operational amplifier
03	OP-15A	Radiation hardened, JFET-input operational amplifier

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

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1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
G	MACY1-X8	8	Can
Н	GDFP1-F10 or CDFP2-F10	10	Flat pack
Р	GDIP1-T8 or CDIP2-T8	8	Dual-in-line

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Positive Voltage (+V _S)	.+22 V dc
Negative supply voltage (-V _S)Storage temperature range	
Maximum power dissipation (P _D) Differential input voltage Input voltage	. ±40 V
Output short circuit duration	Indefinite +300°C
Junction temperature (T _J)	. +150°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Thermal resistance, junction-to-ambient (θ _{JA}) <u>2</u> / Case G Case P Case H	. 119°C/W
4 Recommended operating conditions.	

1.4

Supply voltage (V _S)	±15 V
Ambient operating temperature (T _A)	-55°C to +125°C

1.5 Digital logic testing for device classes Q and V.

Maximum total dose available (dose rate = 50 – 300 rads(Si)/s) 100 Krads 3/

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.

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Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

Derate linearly 6.7 mW/°C above T_A = +75°C for P package; derate linearly 7.1 mW/°C above T_A = +80°C for G package; derate linearly 5.6 mW/ $^{\circ}$ C above $T_A = +70^{\circ}$ C for H package.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-973 - Configuration Management.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be as specified on figure 2.
- 3.3 <u>Electrical performance characteristics and post irradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and post irradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

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TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	$ \begin{array}{c c} \text{Symbol} & \text{Conditions} & \underline{1}/\underline{2}/\underline{3}/\\ & -55^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq +125^{\circ}\text{C}\\ & \text{unless otherwise specified} \\ \end{array} $		Group A subgroups	Device Type	Lir	nits	Unit
	·				Min	Max		
Input offset voltage	Vos	V _{CM} = 0 V		1	01, 03		0.5	mV
				2, 3	1		0.9	
			M,D,P,L,R	1	03		1.0	
				1	02		1.0	
				2, 3			2.0	
Input offset voltage temperature coefficient	TCVOS	-55°C and +1	25°C <u>4</u> /	2, 3	03		10	μV/°C
Input offset current	los	V _S = ±20 V, V	V _{CM} = 0 V <u>5</u> /	1, 3	01, 03		±10	pA
				2	1		±4	nA
			M,D,P,L,R	1	03		±0.3	nA
				1, 3	02		±20	рА
				2			±6	nA
Input bias current	I _{IB}	Vs = ±20 V, V	VCM = 0 V <u>5</u> /	1, 3	01, 03		±50	pA
				2			±5.0	nA
			M,D,P,L,R	1	03		±3.0	nA
				1, 3	02		±100	pA
				2			±7.5	nA
Common mode rejection 4/	CMRR	V _{CM} = IVR =	±10.5 V	1	All	86		dB
ratio		V _{CM} = IVR =	±10.4 V	2, 3		85		
Output voltage swing	Vo	$R_L = 2 k\Omega$		4	All	±11.0		V
			M,D,P,L,R	4	03	±11.0		
		R _L = 10 kΩ		5, 6	All	±12.0		
Large-signal voltage gain	Avo	V _O = ±10 V,	R _L = 2 kΩ	4	01, 03	100		V/mV
				5, 6	1	35		
			M,D,P,L,R	4	03	50		
				4	02	75		
				5, 6]	30		

See footnotes at end of table.

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $\underline{1}/\underline{2}/\underline{3}/$ -55°C \leq T _A \leq +125°C unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Supply current	Icc	V _O = 0 V		1	All		4.0	mA
				2,3			11.0	
			M,D,P,L,R	1	03		4.0	
Power supply rejection 4/	PSRR	V _S = ±10 V to	±18 V	1	All	86		dB
ratio				2,3		85		
Slew rate 4/	SR	A _{VCL} = +1V,		7	01, 03	10		V/μS
		$R_L \ge 2 k\Omega$,		8a		7		
		C _L = 100 pF		7	02	7.5		
		OL = 100 pi		8a		4.5		
Gain bandwidth product 4/	GBW	f _O = 100 KHz	z, T _A = +25°C	7	01, 03	3.5		MHz
		f _O = 87.5 KHz, T _A = +25°C			02	2.5		
Power dissipation	PD	V _O = 0 V, T _A = +25°C		1	All		120	mW
			M,D,P,L,R	1	03		120	
Settling time	ts	<u>6</u> /		9, 10	All		4	μS

- 1/ Devices supplied to this drawing will meet all levels M, D, P, L, R of irradiation. However, this device is only tested at the 'R' level. Pre and Post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level, $T_A = +25$ °C, and $\pm V_S = \pm 15$ V.
- 2/ These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A.
- 3/ $V_S = \pm 15 \text{ V}$, $R_S = 50 \Omega$, unless otherwise specified.
- 4/ This parameter is not tested post-irradiation.
- 5/ Subgroup 3 is guaranteed if not tested.
- 6/ Subgroup 10 is guaranteed if not tested.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

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Г		
Device types	01, 02, and 03	03
Case outlines	G and P	Н
Terminal number	Terminal symbol	
1	BAL	NC
2	-IN	BAL
3	+IN	-IN
4	-V _S	+IN
5	BAL	-V _S
6	OUT	BAL
7	+V _S	VOUT
8	NC	+V _S
9		NC
10		NC

NC = No connection

FIGURE 1. Terminal connections.

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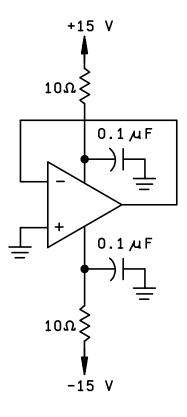


FIGURE 2. Radiation exposure circuit.

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- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M.</u> Device class M devices covered by this drawing shall be in microcircuit group number 61 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V.</u> Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	(in accord	roups lance with 535, table III)
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 4, 5, <u>1</u> / 6, 7, 8a	1, 2, 3, 4, <u>1</u> / 5, 6, 7, 8a	1, 2, 3, <u>1</u> / <u>2</u> / 4, 5, 6, 7, 8a
Group A test requirements (see 4.4)	1, 2, 3, 4, 5, 6, <u>3</u> / 7, 8a, 9, 10	1, 2, 3, 4, <u>3</u> / 5, 6, 7, 8a, 9, 10	1, 2, 3, 4, <u>3</u> / 5, 6, 7, 8a, 9, 10
Group C end-point electrical parameters (see 4.4)	1, 4	1, 4	1, 4
Group D end-point electrical parameters (see 4.4)	1, 4	1, 4	1, 4
Group E end-point electrical parameters (see 4.4)			1

^{1/} PDA applies to subgroup 1. Exclude delta from PDA. (V_{OS} and I_{OS} excluded from PDA for device 01 and 03)

Table IIB. 240 hour burn-in and group C end-point electrical parameters.

Parameter	Device type	Limit	Delta
Vos	03	0.5 mV	±0.5 mV
I _{IB}		±50 pA	±40 pA

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroup 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

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^{2/} See table IIB for delta measurement parameters.

^{3/} Subgroup 10, if not tested, shall be guaranteed to the limits specified in table I herein.

- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - b. $T_A = +125^{\circ}C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes M, Q, and V shall be as specified in MIL-PRF-38535. End-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019 condition A and as specified herein.
 - PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.

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 6.6 Sources of supply. 6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38 The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agree this drawing. 6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-10 The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA. 	d to 3.
The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agree this drawing. 6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-10 The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has beer	d to 3.
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STANDARD SIZE MICROCIRCUIT DRAWING A 5962-895	42
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000 REVISION LEVEL B 12	

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 00-10-23

Approved sources of supply for SMD 5962-89542 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8954201GA	24355	OP-15AJ/883
5962-8954201PA	24355	OP-15AZ/883
5962-8954202GA	24355 <u>3</u> /	OP-15BJ/883
5962-8954203VGA	24355	OP15AJ/QMLV
5962-8954203VHA	24355	OP15AL/QMLV
5962-8954203VPA	24355	OP15AZ/QMLV
5962R8954203VGA	24355	OP15AJ/QMLR
5962R8954203VHA	24355	OP15AL/QMLR
5962R8954203VPA	24355	OP15AZ/QMLR

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ This device has an end-of-life date of 14 April 2001.

Vendor CAGEVendor namenumberand address

24355 Analog Devices

Route 1 Industrial Park PO Box 9106

PO Box 9106 Norwood, MA 02062

Point of contact: 1500 Space Park Drive

P.O. Box 58020

Santa Clara, CA 95052-8020

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.